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PTO/SB/30 (10/2001)

Approved for use through 10/31/2002 OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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REQUEST FOR CONTINUED EXAMINATION (RCE) TRANSMITTAL

Address to:
Commissioner for Patents
Box RCE
Washington, DC 20231

Application Number	09/885,792
Filing Date	6/20/2001
First Named Inventor	Jagannathan et al.
Art Unit	2812
Examiner Name	Christopher W. Lattin
Attorney Docket Number	FIS920000402US1

This is a Request for Continued Examination (RCE) under 37 CFR 1.114 of the above-identified application. Request for Continued Examination (RCE) practice under 37 CFR 1.114 does not apply to any utility or plant application filed prior to June 8, 1995, or to any design application. See Instruction Sheet for RCEs (not to be submitted to the USPTO) on page 2.

1. Submission required under 37 CFR §1.114

a. ☐ Previously submitted

- i. ☐ Consider the amendment(s)/reply under 37 CFR §1.116 previously filed on _____
(Any unentered amendment(s) referred to above will be entered).
- ii. ☐ Consider the arguments in the Appeal Brief or Reply Brief previously filed on _____
- iii. ☐ Other _____

b. ☒ Enclosed

- i. ☒ Amendment/Reply
- ii. ☐ Affidavit(s)/Declaration(s)
- iii. ☐ Information Disclosure Statement (IDS)
- iv. ☐ Other _____

2. Miscellaneous

- a. ☐ Suspension of action on the above-identified application is requested under 37 CFR §1.103(c) for a period of _____ months (Period of suspension shall not exceed 3 months; Fee under 37 CFR §1.17(i) required)
- b. ☐ Other _____

3. Fees

The RCE fee under 37 CFR §1.17(e) is required by 37 CFR §1.114 when the RCE is filed.

- a. ☒ The Director is hereby authorized to charge the following fees, or credit any overpayments, to Deposit Account No. 09-0458
 - i. ☒ RCE fee required under 37 CFR §1.17(e)
 - ii. ☒ Extension of time fee (37 CFR §§1.136 and 1.17)
 - iii. ☒ Other deficiencies
- b. ☐ Check in the amount of \$ _____ enclosed
- c. ☐ Payment by credit card (Form PTO-2038 enclosed)

WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT REQUIRED

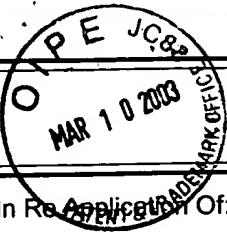
Name (Print / Type)	Olga V. Merkoulouva	Registration No. (Attorney / Agent)	48,757
Signature		Date	03.10.03

CERTIFICATE OF MAILING OR TRANSMISSION

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner For Patents, Box RCE, Washington, DC 20231, or facsimile transmitted to the U.S. Patent and Trademark

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TRANSMITTAL LETTER
(General - Patent Pending)

Docket No.
FIS920000402US1

In Re Application Of: Jagannathan et al.

Serial No.
09/885,792

Filing Date
6/20/2001

Examiner
Christopher W. Lattin

Group Art Unit
2812

Title: A NON-SELF-ALIGNED SI/GE HETEROJUNCTION BIPOLAR TRANSISTOR

TO THE ASSISTANT COMMISSIONER FOR PATENTS:

Transmitted herewith is:

RCE (Request for Continued Examination)
Amendment 1:116

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in the above identified application.

- ☐ No additional fee is required.
- ☐ A check in the amount of _____ is attached.
- ☒ The Assistant Commissioner is hereby authorized to charge and credit Deposit Account No. 09-0458 as described below. A duplicate copy of this sheet is enclosed.
- ☒ Charge the amount of \$750.00
- ☒ Credit any overpayment.
- ☒ Charge any additional fee required.


Signature

Dated: 03.10.03

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703-787-9400



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PATENT TRADEMARK OFFICE

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I certify that this document and fee is being deposited on _____ with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231.

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3-21-03
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Docket No. FIS920000402US1

Basanth Jagannathan

Serial No.:09/885,792

Group Art Unit: No.2812

Filed: June 20, 2001

Examiner: Christopher W. Lattin

For: A NON-SELF-ALIGNED SI/GE
HETEROJUNCTION BIPOLAR
TRANSISTOR

BOX "AF"
RESPONSE UNDER 37 C.F.R. § 1.116.
---EXPEDITE PROCEDURE---
EXAMINING GROUP 2812

Box: Final amendment
Assistant Commissioner of Patents and Trademarks
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.116

Sir:

In response to the Office Action dated December 11, 2002, please amend the above identified application as follows:

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IN THE SPECIFICATION:

A marked-up copy of the changes to selected paragraphs is provided below. A clean copy of these changes is provided in the attached separate sheet, entitled "Clean Version of Changes to Specification". Please replace the marked-up paragraphs with the replacement clean copy of the selected paragraphs attached hereto.

Marked up paragraph at page 7, lines 1-7.

It is another object of the present invention to provide a method for making a heterojunction bipolar transistor which performs low thermal-cycle processing, which, in turn, allows the present method to use thin low-temperature epitaxy (LTE) layers in the formation of base and collector regions. Use of thin LTE layers for these regions increases speed of the transistor and, further, leads to a lowering of the overall topography of the device, making mid-end-of-line (MEOL) processed such as emitter, base, and collector contact opening much easier.

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